



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application. No. : 10/822,345
First Named Inventor : Meng Tao
Filed : April 12, 2004
Title : IMPROVEMENTS FOR SEMICONDUCTOR INTERFACES
Art Unit : 2813
Examiner : Not Yet Assigned

Certificate of Mailing Under 37 CFR 1.8

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INFORMATION DISCLOSURE STATEMENT

Sir:

Pursuant to the provisions of 37 C.F.R. § 1.97, Applicants hereby make of record the references set forth in the attached form PTO/SB/08B. No inference should be made that the cited references are in fact material, are in fact prior art, or that no better art exists. The cited references are listed in numerical order and not in any order based on their pertinence.

It is requested that the Examiner fully consider the cited references and that they be cited on the front of any patent issuing from this application.

Copies of the cited references are attached.

An early action on the merits is respectfully requested.

Respectfully submitted,

Date: Sept 8, 2004

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SEP 13 2004

PTO/SB/08B (08-00)

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Complete if Known

Application Number	10/822,345
Filing Date	April 12, 2004
First Named Inventor	Meng Tao
Group Art Unit	2812
Examiner Name	Not Yet Assigned
Attorney Docket Number	124263-1019

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		R.M. TROMP, R.J. HAMERS, and J.E. DEMUTH, Si(001) dimmer structure observed with scanning tunneling microscopy, Phys. Rev. Lett., 1985, 1303, 55	
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		J.W. LYDING, T.-C SHEN, J.S. HUBACEK, J.R. TUCKER, and G.C. ABELN, Nanoscale patterning and oxidation of H-passivated Si(100)-2x1 surfaces with an ultrahigh vacuum scanning tunneling microscope, Appl. Phys. Lett., 1994, 2010, 64	
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		T.-C. SHEN, C. WANG, and J.R. TUCKER, Al nucleation on monohydride and bare Si (001) surfaces: atomic scale patterning, Phys. Rev. Lett., 1997, 1271, 78	

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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS		
Examiner Initials Name No. 1	Item Description	T ²
	I. LYUBINETSKY, Z. DOHNALEK, W.J. CHOYKE, and J.T. YATES, JR., C1 ₂ dissociation on Si(100)-(2x1): A statistical study by scanning tunneling microscopy, Phys. Rev. B, 1998, 7950, 58	
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